

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	22mΩ @ V _{GS} = 4.5V	7.1A
	26mΩ @ V _{GS} = 2.5V	6.5A
	36mΩ @ V _{GS} = 1.8V	5.5A
	50mΩ @ V _{GS} = 1.5V	4.7A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

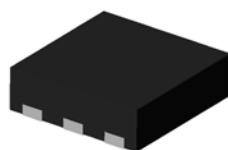
Features

- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

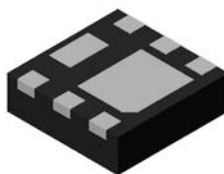
Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.0065 grams (Approximate)

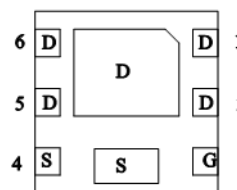
U-DFN2020-6 (Type F)



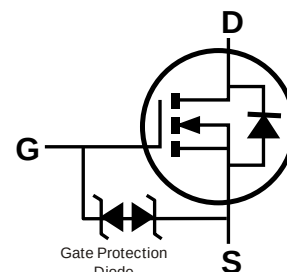
Top View



Bottom View



Pin Out
Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity Per Reel
DMN2024UFDF-7	7	3000
DMN2024UFDF-13	13	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site1



OA = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: F = 2018)

M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



OA = Product Type Marking Code

YWX = Date Code Marking

Y = Year (ex: F = 2018)

W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal code (ex: U = Monday)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	8	9	0	1	2	3	4	5

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	7.1 5.6	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	40	A
Continuous Source-Drain Diode Current			I _S	2.6	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	12	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.96	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	130	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.67	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	75	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	16	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15	22	mΩ	V _{GS} = 4.5V, I _D = 4A
			17	26		V _{GS} = 2.5V, I _D = 4A
			20	36		V _{GS} = 1.8V, I _D = 4A
			23	50		V _{GS} = 1.5V, I _D = 4A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	647	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	78	—		
Reverse Transfer Capacitance	C _{rss}	—	38	—		
Gate Resistance	R _g	—	628	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	7.1	—	nC	V _{DS} = 10V, I _D = 6.5A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	0.9	—		
Gate-Source Charge	Q _{gs}	—	0.7	—		
Gate-Drain Charge	Q _{gd}	—	98	—		
Turn-On Delay Time	t _{D(ON)}	—	140	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _G = 6Ω, R _L = 10Ω, I _D = 1A
Turn-On Rise Time	t _r	—	1024	—		
Turn-Off Delay Time	t _{D(OFF)}	—	434	—		
Turn-Off Fall Time	t _f	—	245	—		
Reverse Recovery Time	t _{RR}	—	149	—	ns	I _F = 1A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	647	—	nC	I _F = 1A, di/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

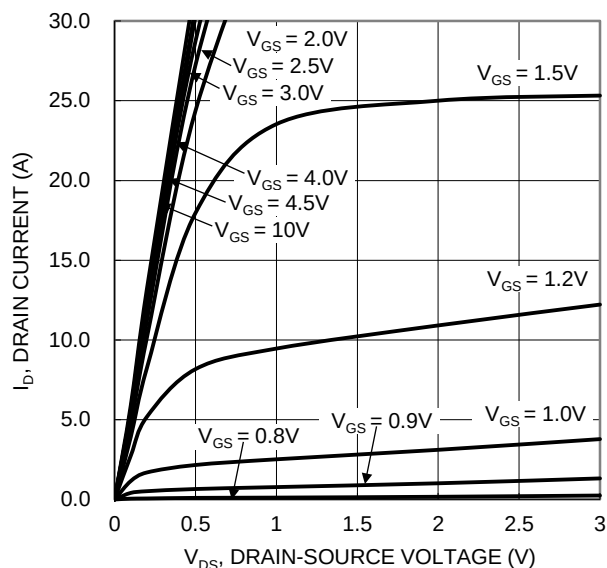


Figure 1. Typical Output Characteristic

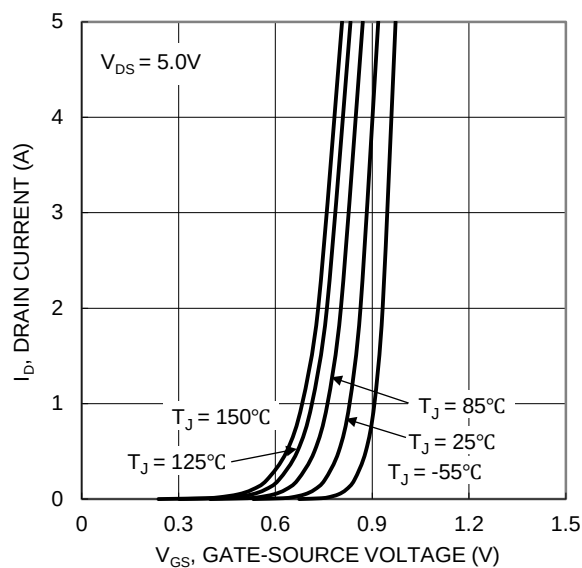


Figure 2. Typical Transfer Characteristic

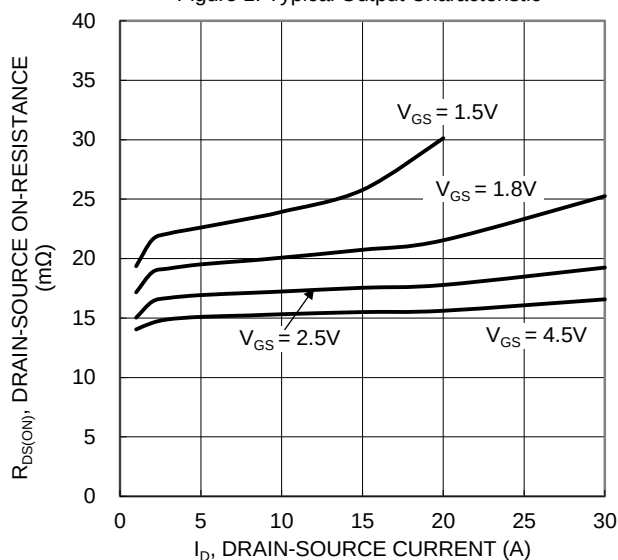


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

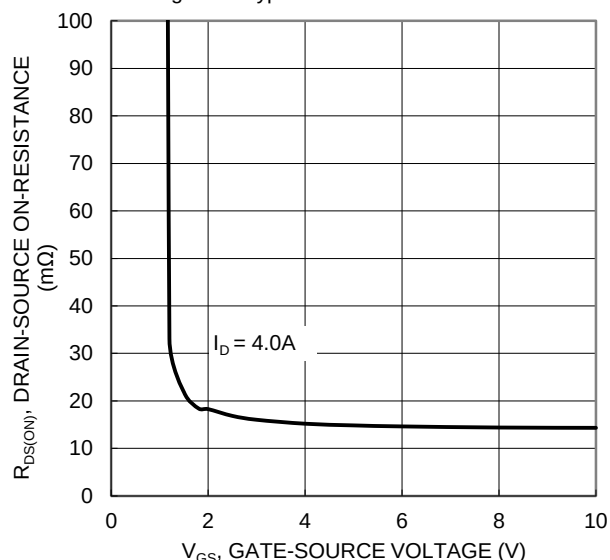


Figure 4. Typical Transfer Characteristic

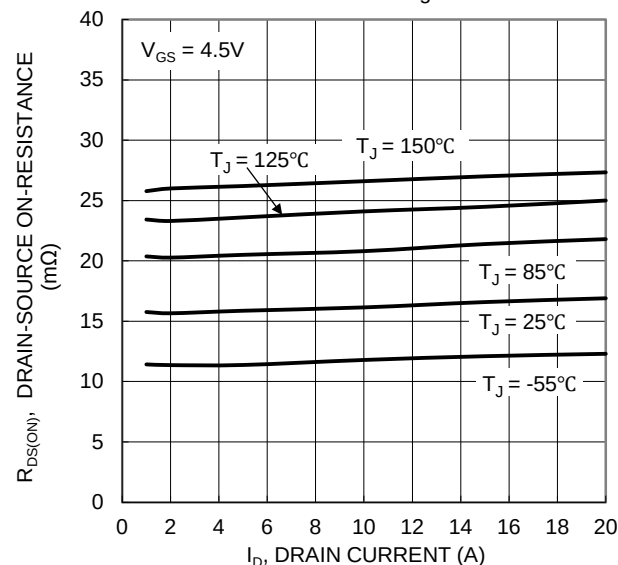


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

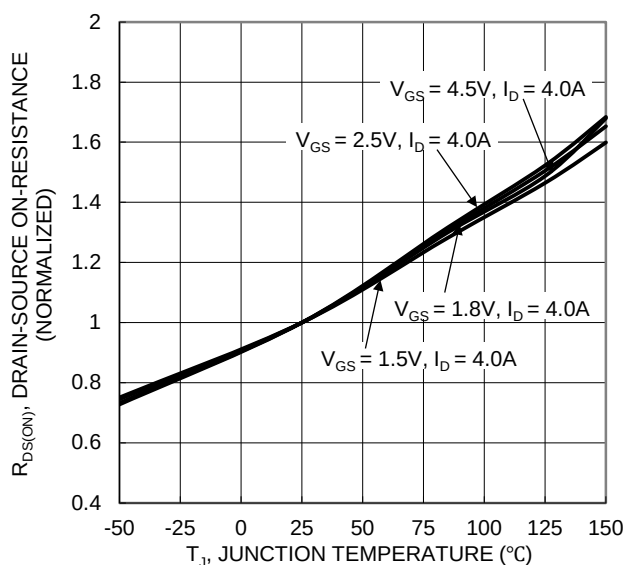


Figure 6. On-Resistance Variation with Temperature

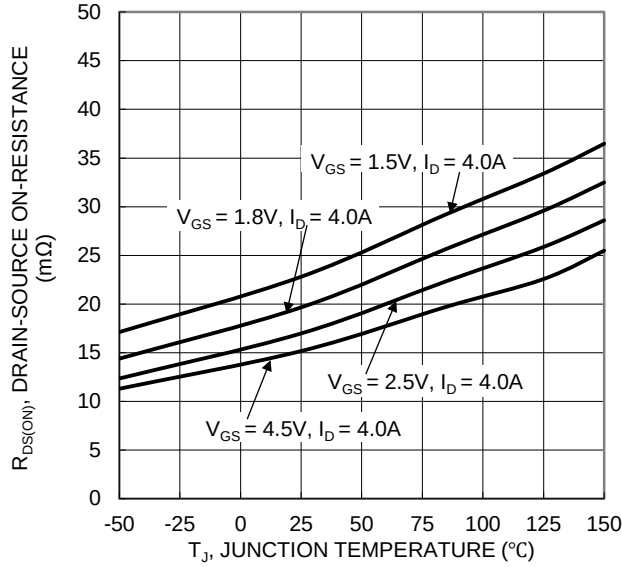


Figure 7. On-Resistance Variation with Temperature

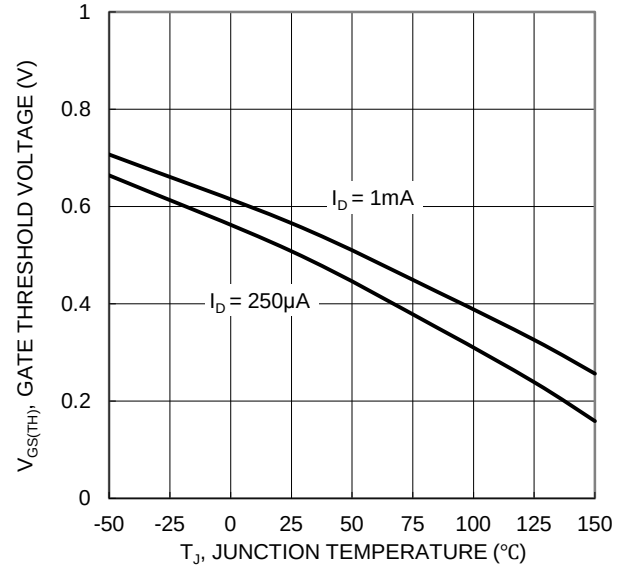


Figure 8. Gate Threshold Variation vs. Junction Temperature

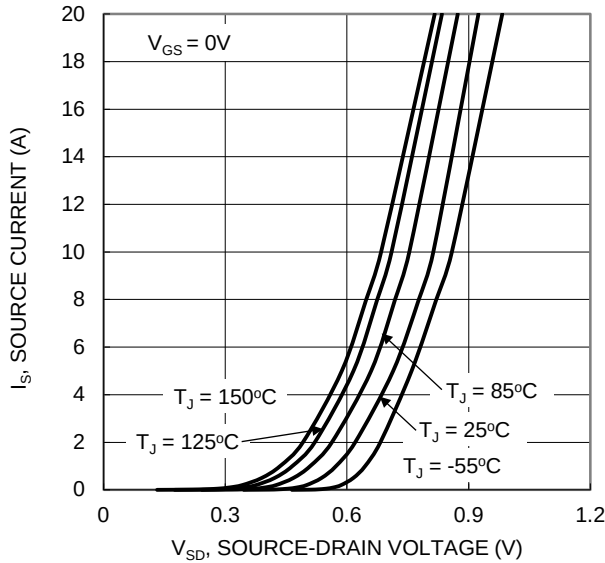


Figure 9. Diode Forward Voltage vs. Current

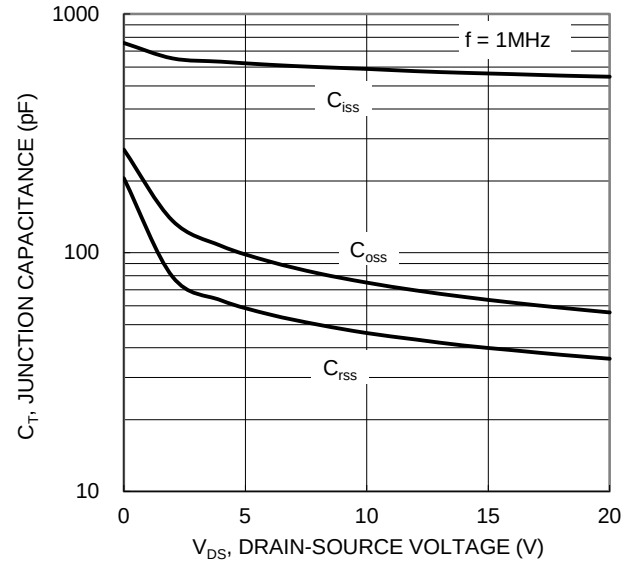


Figure 10. Typical Junction Capacitance

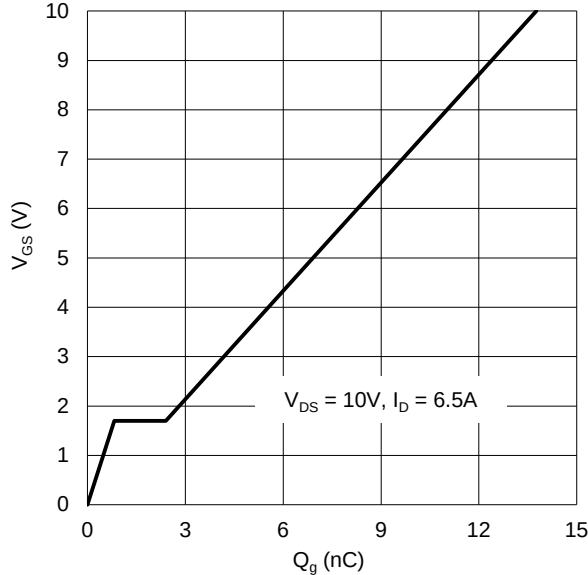


Figure 11. Gate Charge

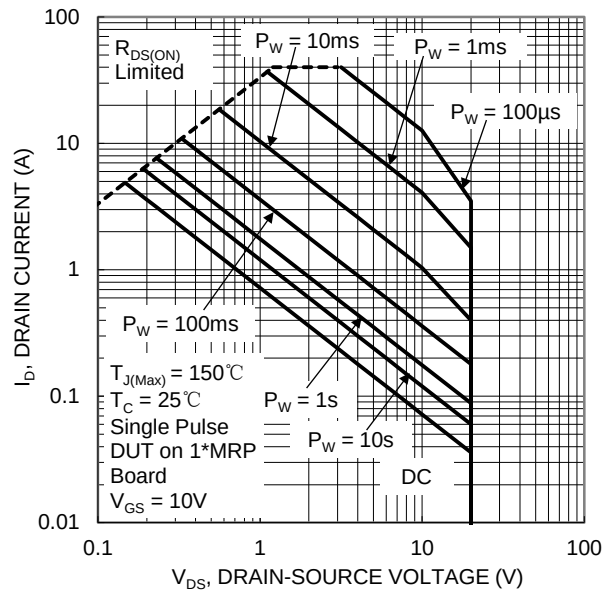


Figure 12. SOA, Safe Operation Area

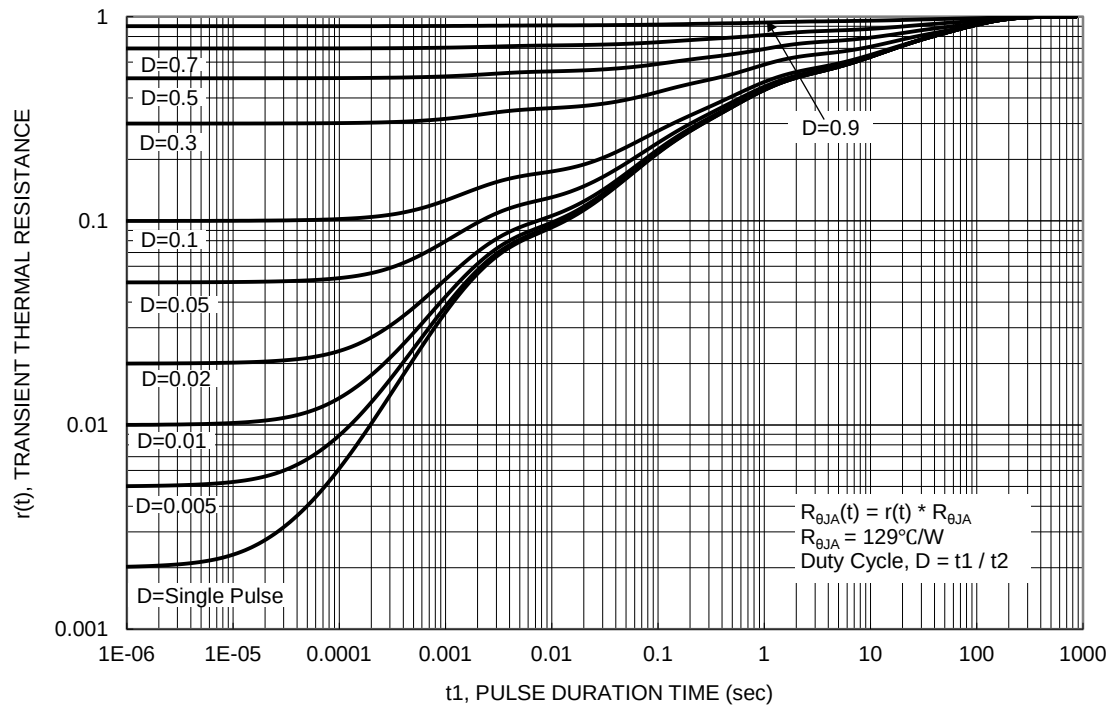
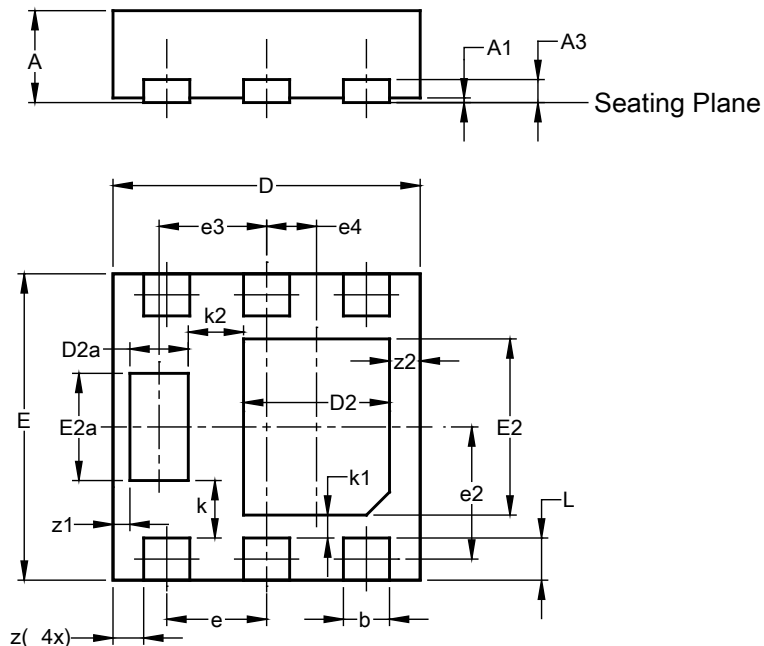


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

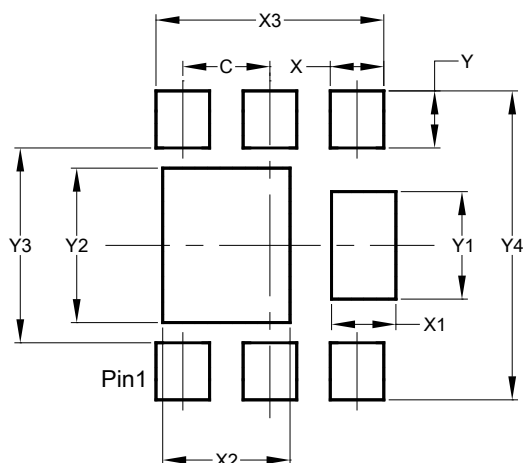


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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